

1S2076A

PRV : 70 Volts
Io : 150 mA

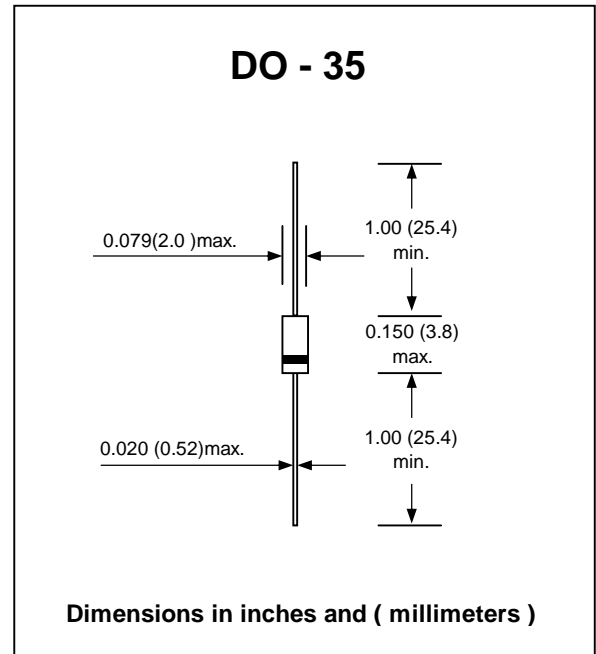
FEATURES :

- * Silicon Epitaxial Planar Diode
- * High reliability
- * Low reverse current
- * Low forward voltage drop
- * High speed switching
- * **Pb / RoHS Free**

MECHANICAL DATA :

- * Case : DO-35 Glass Case
- * Lead : Axial lead solderable per MIL-STD-202, Method 208 guaranteed
- * Polarity : Color band denotes cathode end
- * Mounting position : Any
- * Weight : 0.13 gram (approximately)

HIGH SPEED SWITCHING DIODE



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25 °C ambient temperature unless otherwise specified.
 Single phase, half wave, 60 Hz, resistive or inductive load.
 For capacitive load, derate current by 20%.

RATING	SYMBOL	VALUE	UNIT
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	70	V
Maximum Reverse Voltage	V_R	60	V
Maximum Average Forward Current	$I_{F(AV)}$	150	mA
Maximum Non-Repetitive Peak Forward Current (t < 1s)	I_{FSM}	1.0	A
Maximum Power Dissipation , Ta = 25 °C	P_D	250	mW
Maximum Forward Voltage at $I_F = 10$ mA	V_F	0.8	V
Maximum Reverse Current at $V_R = 30V$	I_R	100	nA
Maximum Reverse Recovery Time (If = 10mA, VR = 6V , RL = 50Ω)	T_{rr}	4.0	ns
Maximum Capacitance Between Lead (VR = 1 V, f = 1MHz)	C	3.0	pF
Junction Temperature Range	T_J	175	°C
Storage Temperature Range	T_{STG}	- 65 to + 175	°C

RATING AND CHARACTERISTIC CURVES (1S2076A)

FIG.1 - DERATING CURVE FOR OUTPUT RECTIFIED CURRENT

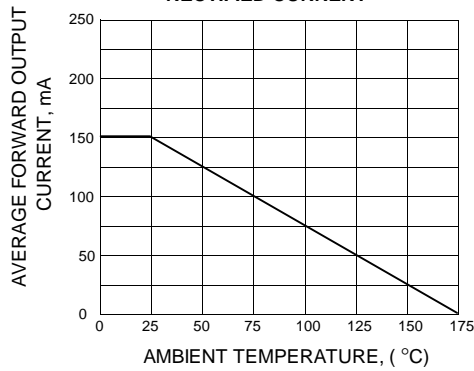


FIG.2 - POWER DERATING CURVE

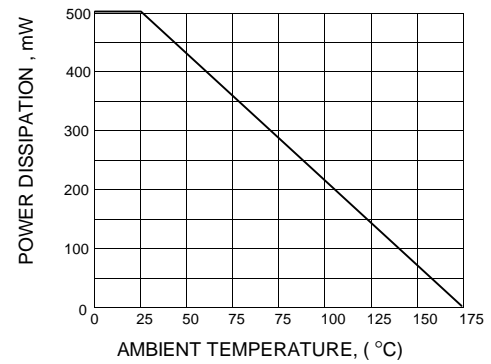


FIG.3 - TYPICAL FORWARD CHARACTERISTICS

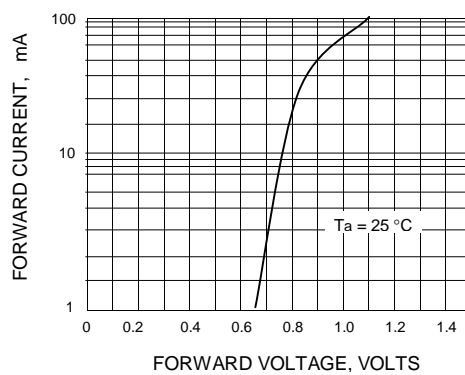


FIG.4 - TYPICAL REVERSE CHARACTERISTICS

